

Addition of an ECTI 2011 Conference Paper: “Design and Implementation of a 1 GHz GaN HEMT Class-F Power Amplifier for Transistor Model Evaluation”

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Declaration of Contributions

Concerning the paper “Design and Implementation of a 1 GHz GaN HEMT Class-F Power Amplifier for Transistor Model Evaluation” published on pages 152 - 155 of the Proceedings of the ECTI Conference 2011 which took place in Khonkaen, Thailand from 17 -19 May, 2011 and also included into IEEE Xplore database, as the authors of the paper mentioned above, we wish to clarify about contributions of authors and other parties to the paper.

Results and discussions in this paper are parts of the first author’s Master Thesis which was majorly done at the Chair of Electromagnetic Theory (ITHE), RWTH Aachen University, Aachen, Germany--an academic partner of the authors’ affiliation. The second author was the formal supervisor of the first author in Thailand. During the work of the first author in Germany, she received elaborate advices from Mr. Christian Lautensack and Mr. Jesus Cumana who are former staffs of the German research institute mentioned above. However, due to differences between our publication policies and Thai regulations for graduate students, Mr. Lautensack and Mr. Cumana are mentioned in the acknowledgement of the paper instead of appearing in the author’s list. Thus, we wish to declare herewith, that the contributions of Mr. Lautensak and Mr. Cumana are at least equal to those of us, the authors of the paper.

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